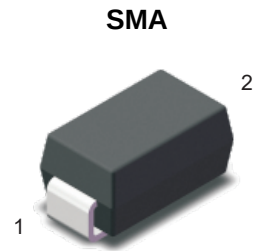


Features

- For surface mount applications
- Glass passivated chip junction
- Fast reverse recovery time
- Low profile package



1.Cathode —|<— 2.Anode

Marking Code:

RS1A-PJ: RS1A
 RS1B-PJ: RS1B
 RS1D-PJ: RS1D
 RS1G-PJ: RS1G
 RS1J-PJ: RS1J
 RS1K-PJ: RS1K
 RS1M-PJ: RS1M

Maximum Ratings and Electrical Characteristics

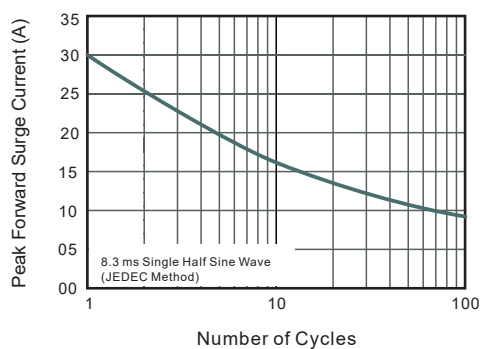
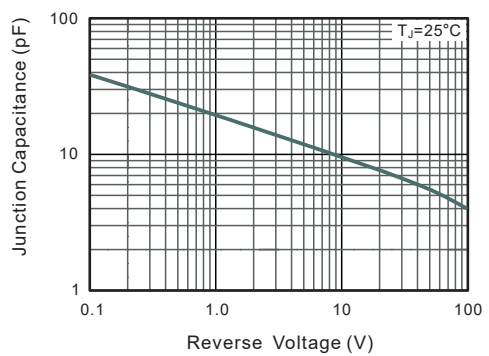
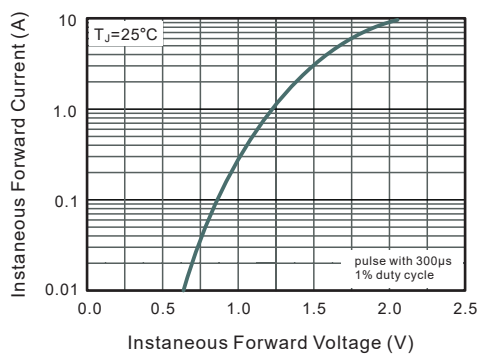
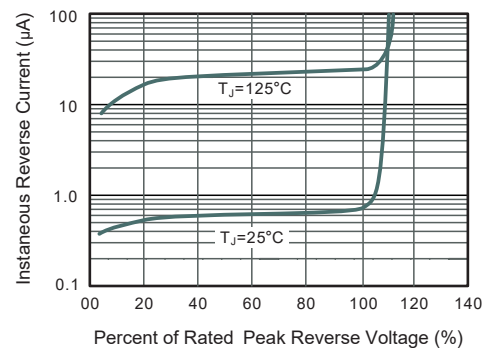
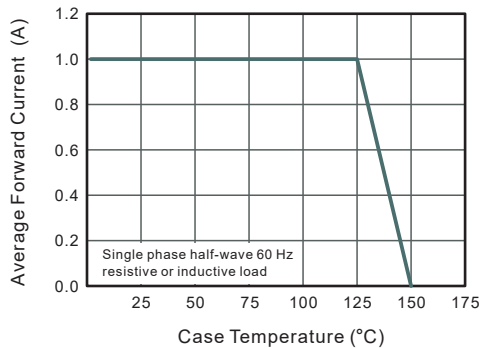
Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	RS1A-PJ	RS1B-PJ	RS1D-PJ	RS1G-PJ	RS1J-PJ	RS1K-PJ	RS1M-PJ	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T _C =125°	I _{F(AV)}	1.0							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I _{FSM}	30							A
Maximum Instantaneous Forward Voltage at 1 A	V _F	1.3							V
Maximum DC Reverse Current at Rated DC Blocking Voltage T _A = 25 °C T _A = 125 °C	I _R	5 50							μA
Typical Junction Capacitance ^{Note1}	C _J	15							pF
Typical Thermal Resistance ^{Note2}	R _{θJA}	75							°C/W
Maximum Reverse Recovery Time ^{Note3}	T _{rr}	150				250	500		nS
Junction Temperature	T _J	150							°C
Storage Temperature Range	T _{STG}	-55 to +150							°C

Note:

1. Measured at 1 MHz and applied reverse voltage of 4 V D.C
2. P.C.B. mounted with 1.0" X 1.0" (2.54 X 2.54 cm) copper pad areas.
3. Measured with $I_F = 0.5 A$, $I_R = 1 A$, $I_{rr} = 0.25 A$

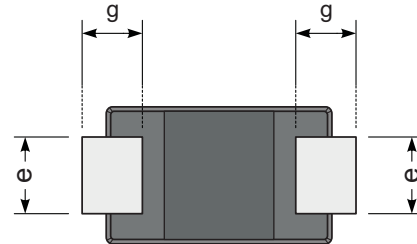
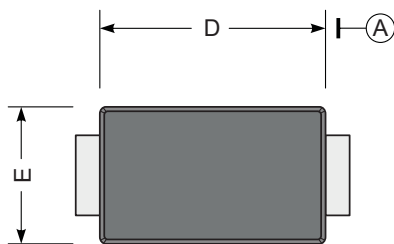
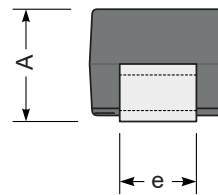
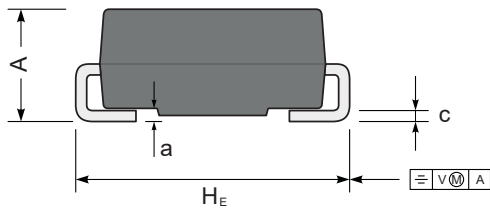
Typical Characteristic Curves



Package Outline

SMA

Dimensions in mm



UNIT		A	D	E	H _E	c	e	g	a
mm	max	2.2	4.5	2.7	5.2	0.31	1.6	1.5	0.3
	min	1.9	4.0	2.3	4.7	0.15	1.3	0.9	
mil	max	87	181	106	205	12	63	59	12
	min	75	157	91	185	6	51	35	